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Q33550xx0xxxx00

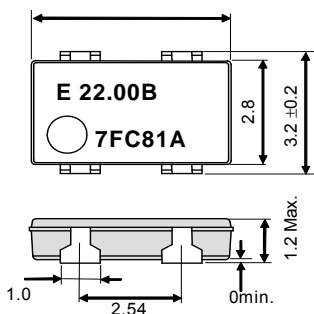
		SG-550SEF	SG-550SDF	SG-550SCF	
	f <sub>o</sub>	2 MHz ~ 48 MHz			
	V <sub>cc</sub>	1.8 V Typ. 1.6 V ~ 2.2 V	2.5 V Typ. 2.2 V ~ 3.0 V	3.3 V Typ. 2.7 V ~ 3.6 V	
	T <sub>stg</sub>	-40 °C ~ +125 °C			
	T <sub>use</sub>	-40 °C ~ +85 °C			
	f <sub>tol</sub>	B: ±50 × 10 <sup>-6</sup> , C: ±100 × 10 <sup>-6</sup> M: ±100 × 10 <sup>-6</sup> L: ±50 × 10 <sup>-6</sup>			-20 °C ~ +70 °C -40 °C ~ +85 °C -40 °C ~ +85 °C
	I <sub>cc</sub>	1.5 mA Max. 1.5 mA Max. 1.5 mA Max. 2.0 mA Max. 2.0 mA Max.	1.5 mA Max. 1.5 mA Max. 2.0 mA Max. 2.0 mA Max. 2.5 mA Max.	1.5 mA Max. 2.0 mA Max. 2.5 mA Max. 2.5 mA Max. 3.5 mA Max.	, 2 MHz ≤ f <sub>o</sub> ≤ 4 MHz , 4 MHz < f <sub>o</sub> ≤ 8 MHz , 8 MHz < f <sub>o</sub> ≤ 16 MHz , 16 MHz < f <sub>o</sub> ≤ 25 MHz , 25 MHz < f <sub>o</sub> ≤ 33 MHz , 33 MHz < f <sub>o</sub> ≤ 48 MHz
	I <sub>std</sub>	0.7 μA Max.	1.5 μA Max.	2.0 μA Max.	ST = GND
	SYM	45 % ~ 55 % 40 % ~ 60 %	45 % ~ 55 % 40 % ~ 60 %		2 MHz ≤ f <sub>o</sub> ≤ 16 MHz 16 MHz < f <sub>o</sub> ≤ 40 MHz 40 MHz < f <sub>o</sub> ≤ 48 MHz
	V <sub>OH</sub>	90 % V <sub>cc</sub> Min.			I <sub>OH</sub> = -3 mA
	V <sub>OL</sub>	10 % V <sub>cc</sub> Max.			I <sub>OL</sub> = 3 mA
CMOS	L <sub>CMOS</sub>	15 pF Max.			
	V <sub>IH</sub>	80 % V <sub>cc</sub> Min.			ST
	V <sub>IL</sub>	20 % V <sub>CC</sub> Max.			
/	tr / tf	4 ns Max.			20 % V <sub>cc</sub> ~ 80 % V <sub>cc</sub> , L <sub>CMOS</sub> = 15 pF
	t <sub>str</sub>	10 ms Max.			90 % V <sub>cc</sub> 0
	f <sub>aging</sub>	±5 × 10 <sup>-6</sup> / year Max.			+25 °C, V <sub>cc</sub> = 1.8 V, 2.5 V, 3.3 V

SG-550 S E F 22.000000MHz B

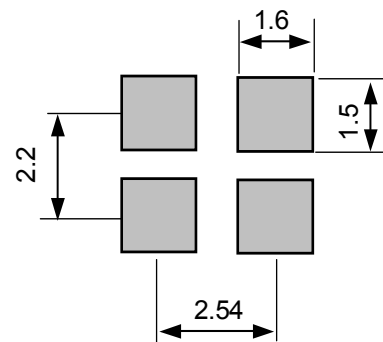
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mm



1	ST
2	GND
3	OUT
4	V <sub>cc</sub>



ST  
ST = " H  
ST = " L

V<sub>cc</sub>-GND

0.01~0.1uF

PDCA  
 ISO14001  
 ISO14001

ISO 14000 1996

Seiko Epson  
 ISO 9000  
 ISO 9001  
 16949

ISO/TS

ISO/TS16949 , ISO9001

	
	<b>RoHS</b> RoHS
	
	

Seiko Epson	Seiko Epson
1.	2.
4.	5.
6.	7.
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3.	